

Japanese Unexamined Patent Application Publication No. 3-238863

SPECIFICATION <EXCERPT>

In FIG. 1, on a upper-side position of photoelectric conversion N⁻ layer 4 of the base film 9 having a thickness of several μ m to 10 μ m, a circular or square oxide film 12 made of SiO₂ as a transparent film by the plasma CVD method. Then tetraethoxysilane (hereinafter, referred to as TEOS) that is organic silane is deposited on the oxide film 12 to form light-receiving lens 13 having a convex lens shape.